



DMT10H009SK3

### **Product Summary**

BV <sub>DSS</sub>	Rds(on) Max	I⊵ Max Tc = +25°C
100V	9.1mΩ @ V <sub>GS</sub> = 10V	91A

### Description

This new generation MOSFET features low on-resistance and fast switching, making it ideal for high efficiency power management applications.

# **Applications**

- Power Management Functions
- DC-DC Converters
- Backlighting

### **100V N-CHANNEL ENHANCEMENT MODE MOSFET**

### Features

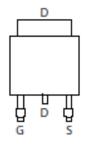
- 100% Unclamped Inductive Switching Ensures More Reliable and Robust End Application
- Low RDS(ON) Minimizes Power Losses
- Low Qg –Minimizes Switching Losses
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/quality/product-definitions/</u>

### **Mechanical Data**

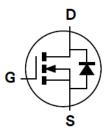
- Case: TO252
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 3 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe Solderable per MIL-STD-202, Method 208 (€3)
- Weight: 0.33 grams (Approximate)



Top View



Pin Out Top View



Equivalent Circuit

### Ordering Information (Note 4)

Case	Packaging
TO252 (DPAK)	2500/Tape & Reel

1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.

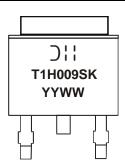
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

### **Marking Information**

Notes:



J = Manufacturer's Marking
T1H009SK = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 19 = 2019)
WW = Week Code (01 to 53)



### Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	VDSS	100	V	
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current Mar. 10M	Tc = +25°C	- ID	91	А
Continuous Drain Current, V <sub>GS</sub> = 10V	$T_{\rm C} = +70^{\circ}{\rm C}$		75	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		Ідм	360	A
Maximum Continuous Body Diode Forward Current (Note 6)		ls	91	A
Avalanche Current, L = 3mH (Note 8)		I <sub>AS</sub>	11	A
Avalanche Energy, L = 3mH (Note 8)		E <sub>AS</sub>	181	mJ
V <sub>DS</sub> Spike, L = 0.1mH	t = 10μs	VSPIKE	120	V

# Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
Total Power Dissipation (Note 5)		PD	1.7	W	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	RθJA	73	°C/W	
Total Power Dissipation (Note 6)		PD	3.2	W	
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	RθJA	39	°C/W	
Thermal Resistance, Junction to Case		Rejc	1.1	°C/vv	
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C	

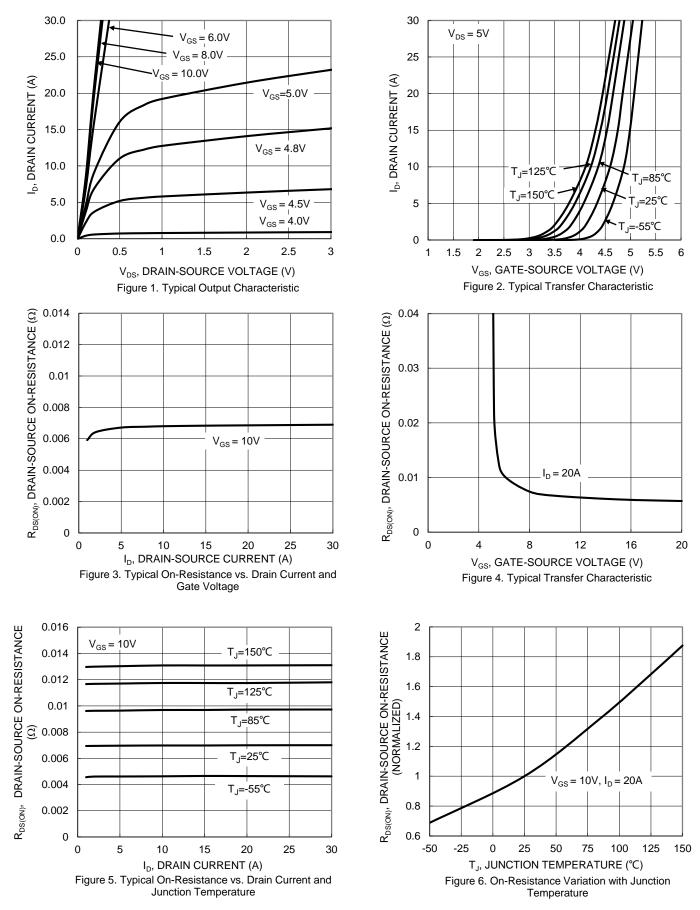
## Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)				1	•		
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	100	—	_	V	$V_{GS} = 0V, I_D = 1mA$	
Zero Gate Voltage Drain Current	IDSS	_	_	1	$\mu A$ $V_{DS} = 80V, V_{GS} = 0V$		
Gate-Source Leakage	lgss	_	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	VGS(TH)	2	_	4	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	RDS(ON)	—	6.9	9.1	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A	
Diode Forward Voltage	V <sub>SD</sub>	_	0.8	1.3	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	Ciss		2028			$V_{DS} = 50V, V_{GS} = 0V$ f = 1MHz	
Output Capacitance	Coss		546		pF		
Reverse Transfer Capacitance	Crss	—	11	_			
Gate Resistance	Rg	0.4	1.7	3.4	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$	
Total Gate Charge	Qg	_	34	_		$V_{DD} = 50V, I_D = 13A,$ $V_{GS} = 10V$	
Gate-Source Charge	Qgs	_	6	_	nC		
Gate-Drain Charge	Qgd		12				
Turn-On Delay Time	tD(ON)		8.3			$V_{DD} = 50V, V_{GS} = 10V,$ $I_D = 13A, R_g = 6\Omega$	
Turn-On Rise Time	tR		15.9				
Turn-Off Delay Time	tD(OFF)	_	27.6	_	ns		
Turn-Off Fall Time	t <sub>F</sub>	_	21.3	—	1		
Reverse Recovery Time	trr	_	47	_	ns		
Reverse Recovery Charge	Q <sub>RR</sub>	_	72	_	nC	IF = 13A, di/dt = 100A/µs	

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing. Notes:



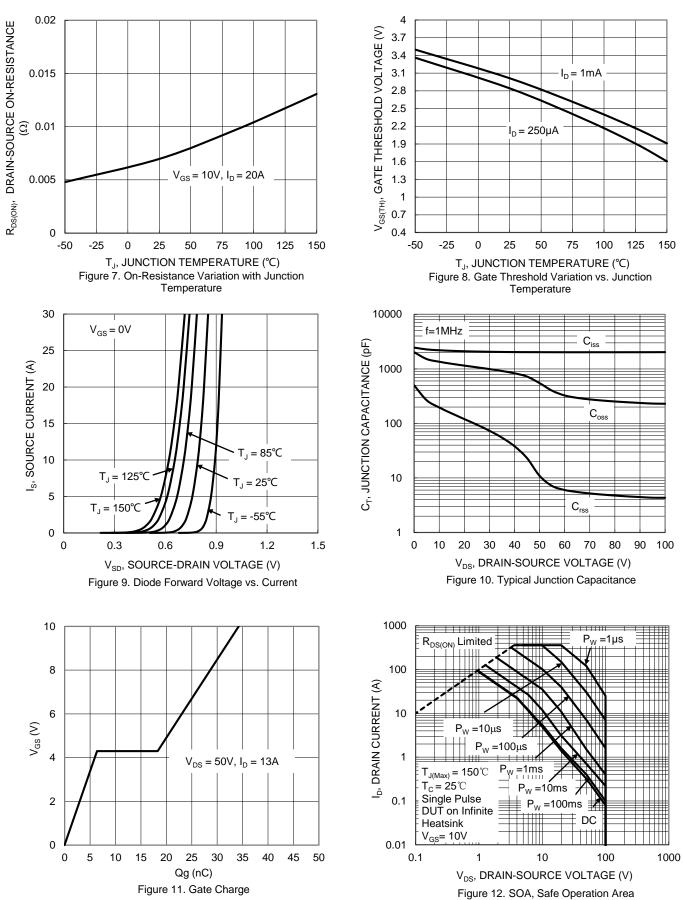
### DMT10H009SK3



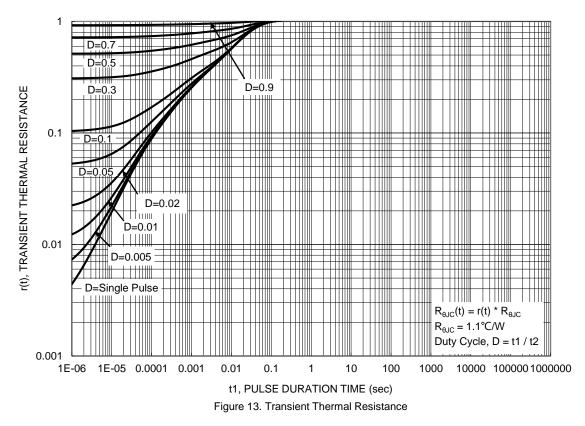
DMT10H009SK3 Document number: DS42154 Rev. 3 - 2



### DMT10H009SK3



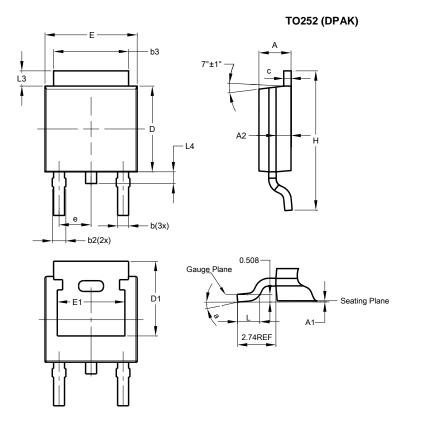






## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

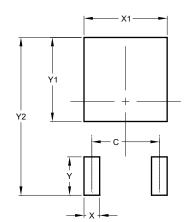


TO252 (DPAK)						
Dim	Min	Max	Тур			
Α	2.19	2.39	2.29			
A1	0.00	0.13	0.08			
A2	0.97	1.17	1.07			
q	0.64	0.88	0.783			
b2	0.76	1.14	0.95			
b3	5.21	5.46	5.33			
С	0.45	0.58	0.531			
D	6.00	6.20	6.10			
D1	5.21	-	-			
е	-	-	2.286			
Е	6.45	6.70	6.58			
E1	4.32	-	-			
Н	9.40	10.41	9.91			
L	1.40	1.78	1.59			
L3	0.88	1.27	1.08			
L4	0.64	1.02	0.83			
а	0°	10°	-			
All Dimensions in mm						

# **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### TO252 (DPAK)



Dimensions	Value (in mm)			
С	4.572			
Х	1.060			
X1	5.632			
Y	2.600			
Y1	5.700			
Y2	10.700			



### IMPORTANT NOTICE

DIODES INCORPORATED MAKES NO WARRANTY OF ANY KIND, EXPRESS OR IMPLIED, WITH REGARDS TO THIS DOCUMENT, INCLUDING, BUT NOT LIMITED TO, THE IMPLIED WARRANTIES OF MERCHANTABILITY AND FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION).

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to this document and any product described herein. Diodes Incorporated does not assume any liability arising out of the application or use of this document or any product described herein; neither does Diodes Incorporated convey any license under its patent or trademark rights, nor the rights of others. Any Customer or user of this document or products described herein in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on Diodes Incorporated website, harmless against all damages.

Diodes Incorporated does not warrant or accept any liability whatsoever in respect of any products purchased through unauthorized sales channel. Should Customers purchase or use Diodes Incorporated products for any unintended or unauthorized application, Customers shall indemnify and hold Diodes Incorporated and its representatives harmless against all claims, damages, expenses, and attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized application.

Products described herein may be covered by one or more United States, international or foreign patents pending. Product names and markings noted herein may also be covered by one or more United States, international or foreign trademarks.

This document is written in English but may be translated into multiple languages for reference. Only the English version of this document is the final and determinative format released by Diodes Incorporated.

#### LIFE SUPPORT

Diodes Incorporated products are specifically not authorized for use as critical components in life support devices or systems without the express written approval of the Chief Executive Officer of Diodes Incorporated. As used herein:

- A. Life support devices or systems are devices or systems which:
  - 1. are intended to implant into the body, or
  - 2. support or sustain life and whose failure to perform when properly used in accordance with instructions for use provided in the labeling can be reasonably expected to result in significant injury to the user.
- B. A critical component is any component in a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or to affect its safety or effectiveness.

Customers represent that they have all necessary expertise in the safety and regulatory ramifications of their life support devices or systems, and acknowledge and agree that they are solely responsible for all legal, regulatory and safety-related requirements concerning their products and any use of Diodes Incorporated products in such safety-critical, life support devices or systems, notwithstanding any devices- or systems-related information or support that may be provided by Diodes Incorporated. Further, Customers must fully indemnify Diodes Incorporated and its representatives against any damages arising out of the use of Diodes Incorporated products in such safety-critical, life support devices or systems.

Copyright © 2019, Diodes Incorporated

www.diodes.com